

23rd JSAP Awards

The JSAP (the Japan Society of Applied Physics) Awards are given to recognize outstanding achievements in the field of applied physics for papers published in JSAP and IPAP (the Institute of Pure and Applied Physics) publications: Japanese Journal of Applied Physics (JJAP) and membership journal "OYO BUTSURI". There are three categories of the Awards: JJAP Awards for the Best Original Paper, JJAP Awards for the Most Promising Young Scientist, and JSAP Award for the Best Review Paper. Applications for the Awards were solicited from the candidates themselves or appropriate recommendations.

The JSAP decided themselves the winners of each award listed below. The awards recipients had a commemorative talk during the 62nd Autumn Meeting of the Japan Society of Applied Physics, September 2001.

Recipients List

1. Award for the Best Original Paper

Recipients:

Naoko YANASE, Kazuhide ABE,
Noburu FUKUSHIMA and Takashi KAWAKUBO
Advanced LSI Technology Laboratory, R&D Center, Toshiba Corporation
Thickness Dependence of Ferroelectricity in Heteroepitaxial BaTiO₃ Thin Film Capacitors
Jpn. J. Appl. Phys. Vol.38 (1999) 5305-5308.

2. Award for the Most Promising Young Scientist

(1) Yuzo ISHII

NTT Telecommunications Energy Laboratories
Ink-Jet Fabrication of Polymer Microlens for Optical-I/O Chip Packaging
Jpn. J. Appl. Phys. Vol.39 (2000) 1490-1493.

(2) Ken-ichi KAWAMURA

Hosono Transparent Electro-Active Materials (TEAM) Project, Exploratory Research for Advanced Technology, Japan Science and Technology Corporation
Holographic Encoding of Permanent Gratings Embedded in Diamond by Two Beam Interface of a Single Femtosecond Near-Infrared Laser Pulse
Jpn. J. Appl. Phys. Vol.39 (2000) L767-L769.

(3) Hideyuki WATANABE

Electrotechnical Laboratory (Present: National Institute of Advanced Industrial Science and Technology)
Nonlinear Effects Excitonic Emission from High Quality Homoepitaxial Diamond Films
Jpn. J. Appl. Phys. Vol.39 (2000) L835-L837.

(4) Takashi SUEMASU

Institute of Applied Physics, University of Tsukuba
Room Temperature 1.6 μ m Electroluminescence from a Si-Based Light Emitting Diode with β -FeSi₂ Active Region
Jpn. J. Appl. Phys. Vol.39 (2000) L1013-L1015.

(5) Ryoji FUNAHASHI

Osaka National Research Institute (Present: National Institute of Advanced Industrial Science and Technology)
An Oxide Single Crystal with High Thermoelectric Performance in Air
Jpn. J. Appl. Phys. Vol.39 (2000) L1127-L1129

3. Award for the Best Review Paper

Recipients:

Seiji SAMUKAWA*, Vincent M. Donnelly,**
Mikhali V. Malyshev**

Silicon Systems Research Laboratories, NEC Corporation, **Bell Laboratories, Lucent Technologies (*Present: Tohoku University)
Effects of Discharge Frequency in Plasma Etching and Ultra-high-Frequency Plasma Source for High-Performance Etching for Ultralarge-Scale Integrated Circuits
Jpn. J. Appl. Phys. Vol.39 (2000) 1583-1596.